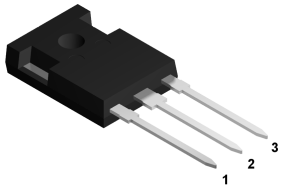
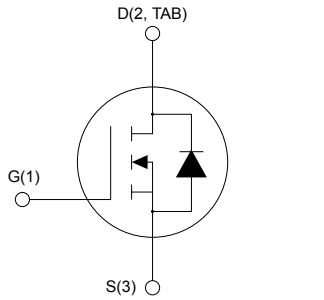
STWA60N028T

Datasheet

N-channel 600 V, 22 mΩ typ., 84 A STMESH trench T Power MOSFET in a TO-247 long leads package



TO-247 long leads



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STWA60N028T	600 V	28 mΩ	84 A

- Very low FOM ($R_{DS(on)} \cdot Q_g$)
- Excellent stability and uniformity
- Low gate charge, input capacitance and resistance
- Exellent switching performance
- 100% avalanche tested

Application

- Microinverter
- Power supplies and converters

Description

This N-channel Power MOSFET is based on the most innovative STMESH trench T technology, suitable for medium to high-voltage MOSFETs. It features outstanding low on-resistance and reduced gate charge values, thus minimizing conduction losses. The product delivers excellent switching performance and robust avalanche capability. The T series is designed for high power density applications, ensuring the highest efficiency standards.

Product status link
STWA60N028T

Product summary	
Order code	STWA60N028T
Marking	60N028T
Package	TO-247 long leads
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±30	V
I_D	Drain current (continuous) at T_C = 25 °C	84	A
	Drain current (continuous) at T_C = 100 °C	53	
I_{DM}(1)	Drain current (pulsed)	391	A
P_{TOT}	Total power dissipation at T_C = 25 °C	481	W
dv/dt(2)	Peak diode recovery voltage slope	15	V/ns
dv/dt(3)	MOSFET dv/dt ruggedness	100	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range		°C

1. *Pulse width is limited by safe operating area.*
2. *I_{SD} ≤ 42 A, V_{DS} (peak) < $V_{(BR)DSS}$, V_{DD} = 400 V.*
3. *V_{DD} = 480 V.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.26	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or non-repetitive (pulse width limited by T_J max.)	12	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	1300	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified.

Table 4. On/off-states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	600			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V			5	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_C = 125 °C(1)			200	
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3.2	3.7	4.2	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 42 A		22	28	mΩ

1. *Specified by design, not tested in production.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 400 V, f = 250 kHz, V_{GS} = 0 V	-	9100	-	pF
C_{oss}	Output capacitance		-	183	-	pF
$C_{oss\ eq.}$(1)	Equivalent output capacitance	V_{DS} = 0 to 400 V, V_{GS} = 0 V	-	1531	-	pF
R_g	Intrinsic gate resistance	f = 250 kHz, open drain	-	1	-	Ω
Q_g	Total gate charge	V_{DD} = 400 V, I_D = 42 A, V_{GS} = 0 to 10 V (see Figure 14. Test circuit for gate charge behavior)	-	164	-	nC
Q_{gs}	Gate-source charge		-	42	-	nC
Q_{gd}	Gate-drain charge		-	40	-	nC

1. *$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to stated value.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD}= 300 V, I_D = 42 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	38	-	ns
t_r	Rise time		-	45	-	ns
$t_{d(off)}$	Turn-off delay time		-	125	-	ns
t_f	Curreny fall time		-	3	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		84	A
I_{SDM}(1)	Source-drain current (pulsed)		-		391	A
V_{SD}(2)	Forward on voltage	I_{SD} = 84 A, V_{GS} = 0 V	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 84 A, di/dt = 100 A/µs, V_{DD} = 60 V (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	534		ns
Q_{rr}	Reverse recovery charge		-	13.9		µC
I_{RRM}	Reverse recovery current		-	52		A
t_{rr}	Reverse recovery time	I_{SD} = 84 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_J = 150 °C (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	665		ns
Q_{rr}	Reverse recovery charge		-	21		µC
I_{RRM}	Reverse recovery current		-	60		A

1. *Pulse width is limited by safe operating area.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

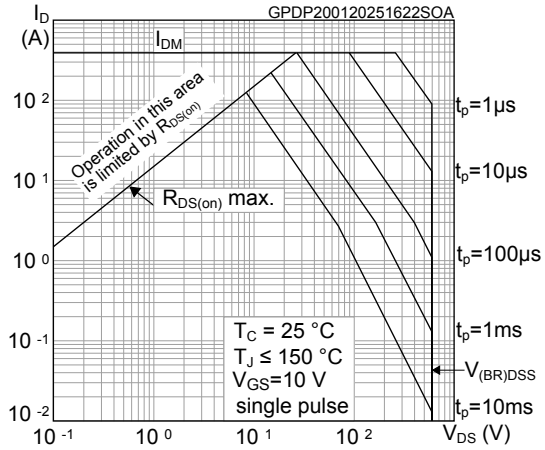


Figure 2. Maximum transient thermal impedance

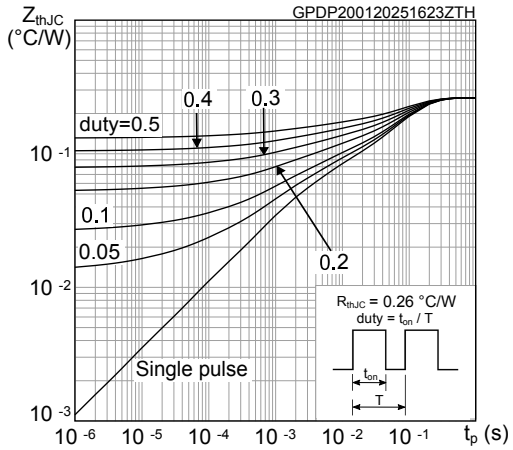


Figure 3. Typical output characteristics

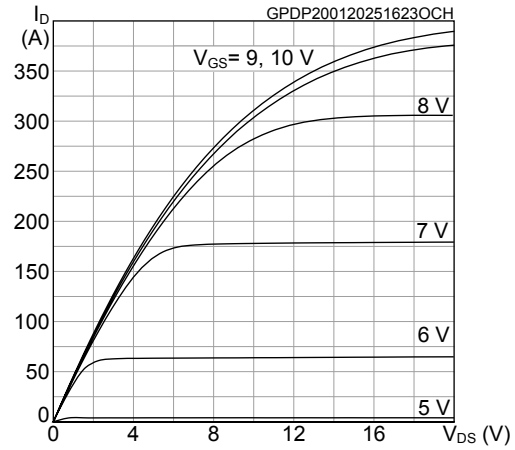


Figure 4. Typical transfer characteristics

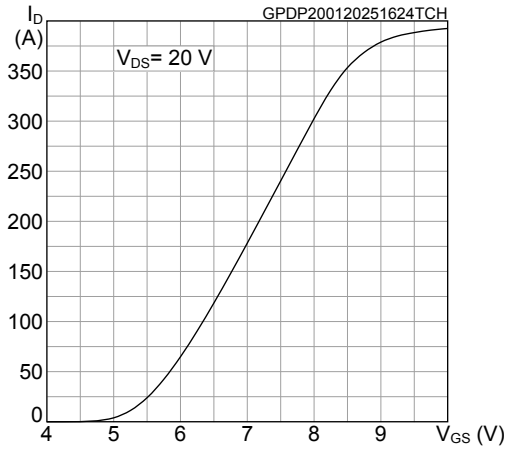


Figure 5. Typical gate charge characteristics

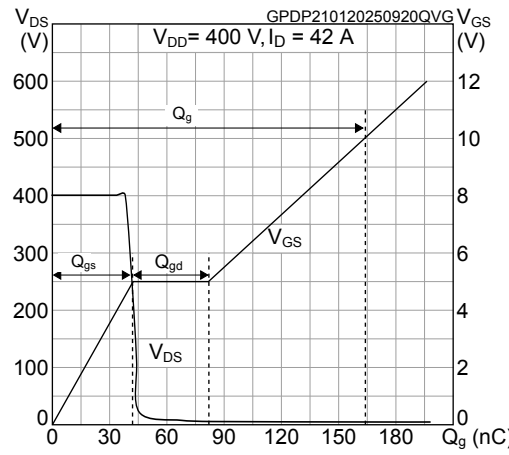


Figure 6. Typical capacitance characteristics

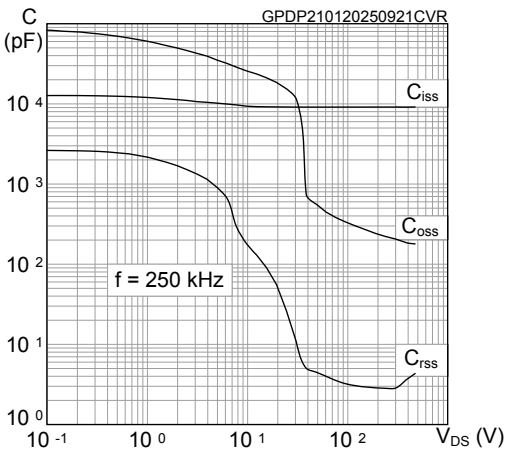


Figure 7. Typical drain-source on-resistance

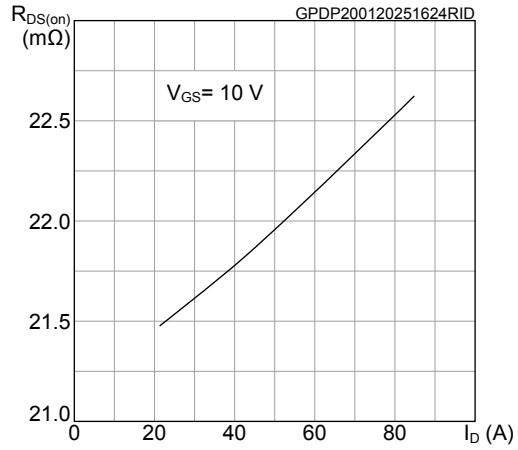


Figure 8. Normalized on-resistance vs temperature

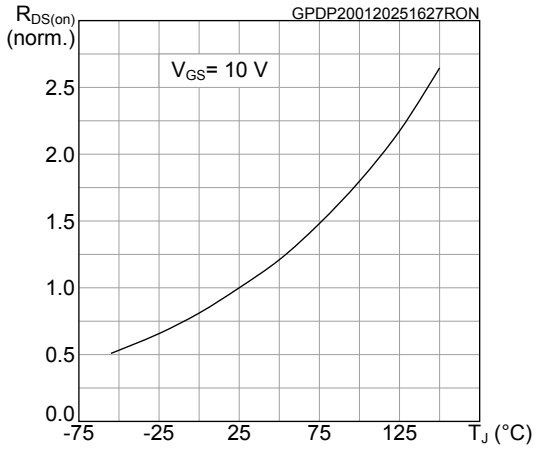


Figure 9. Normalized gate threshold vs temperature

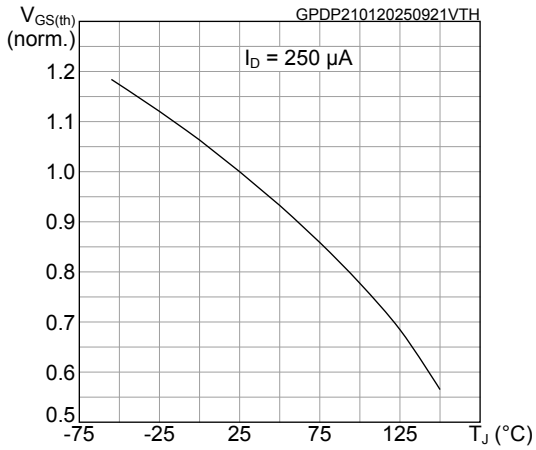


Figure 10. Normalized breakdown voltage vs temperature

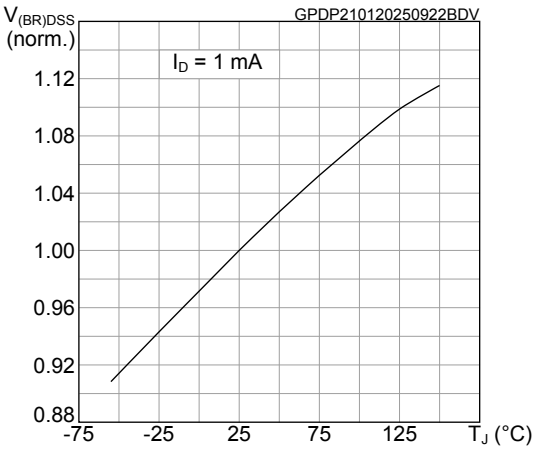


Figure 11. Typical reverse diode forward characteristics

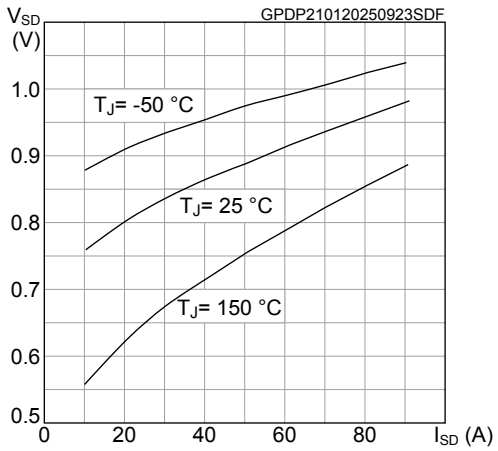
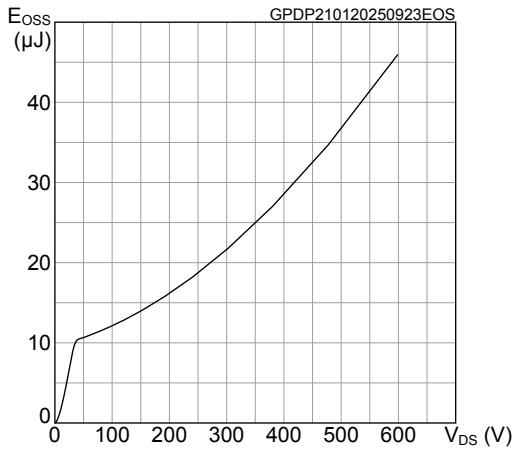


Figure 12. Typical output capacitance stored energy



3 Test circuits

Figure 13. Test circuit for resistive load switching times

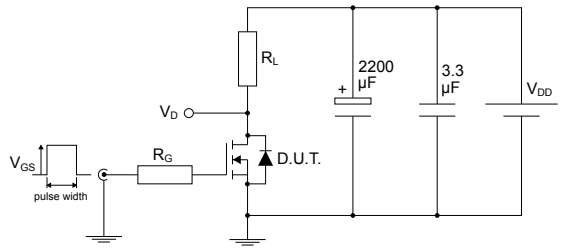


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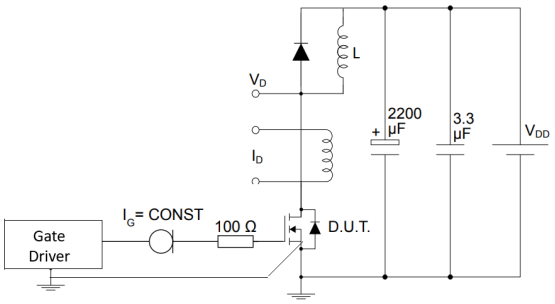
Figure 14. Test circuit for gate charge behavior



GPDP191120241113SA

Figure 15. Test circuit for inductive load switching and diode recovery times

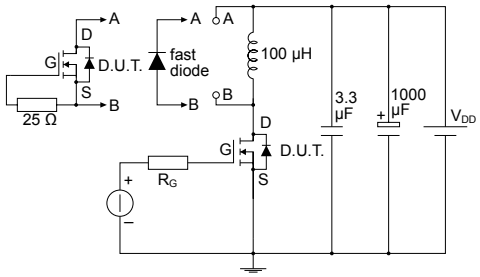


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Figure 16. Unclamped inductive load test circuit

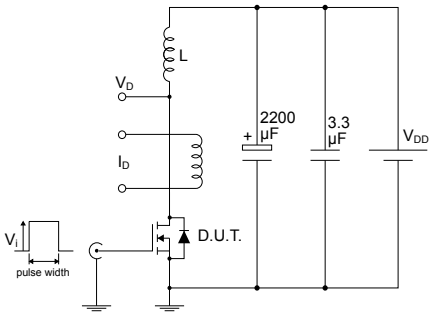

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Figure 17. Unclamped inductive waveform

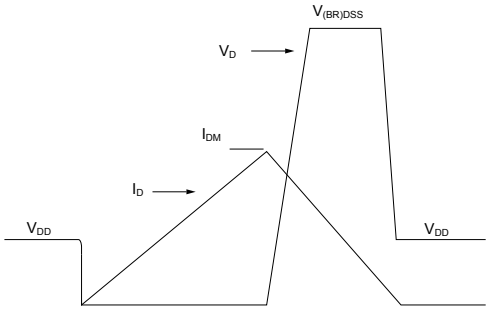

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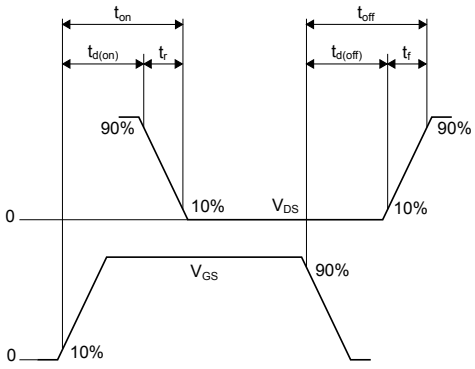
Figure 18. Switching time waveform



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4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-247 long leads package information

Figure 19. **TO-247 long leads package outline**

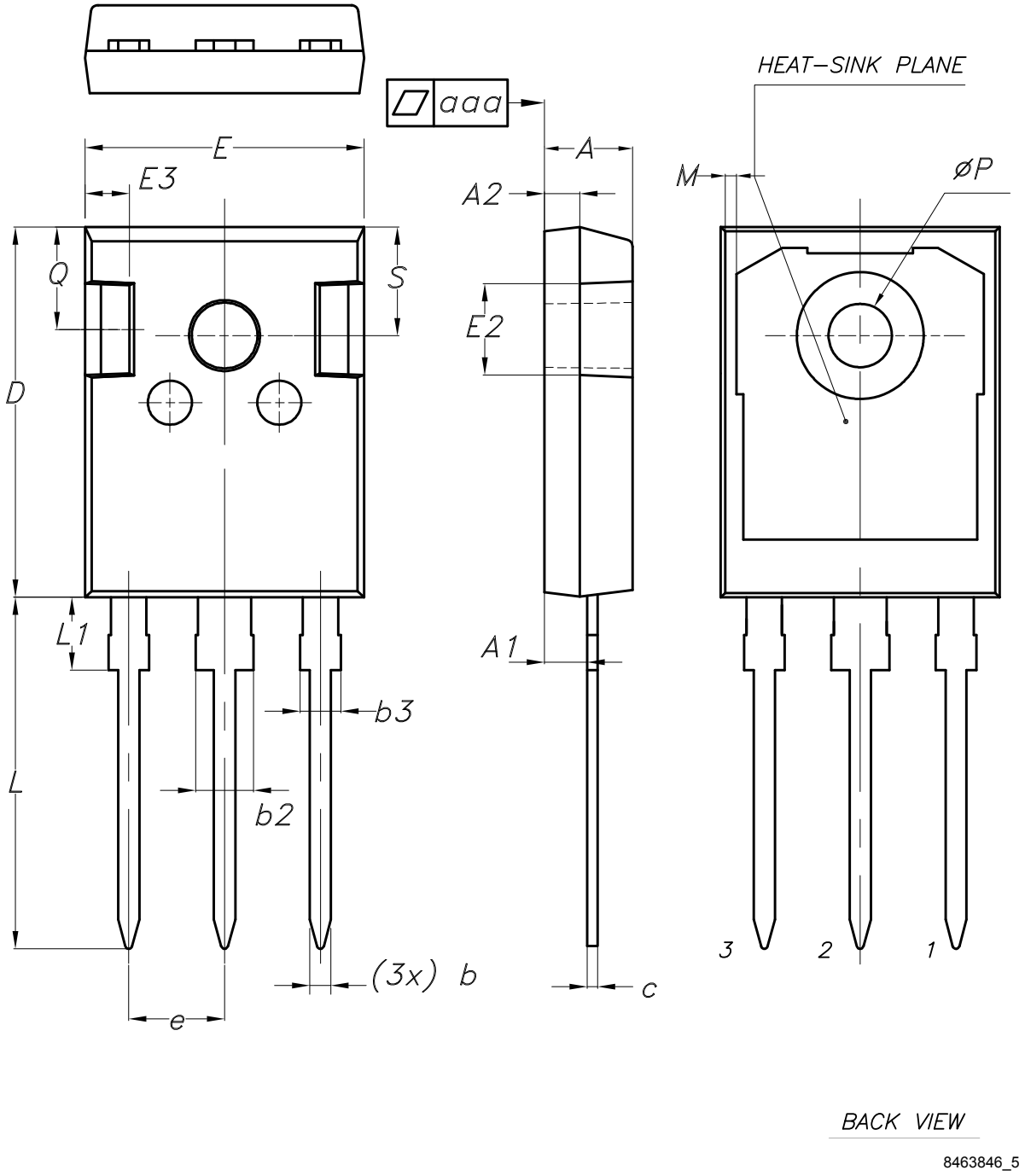

Table 8. **TO-247 long leads package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.26
b2			3.25
b3			2.25
c	0.59		0.66
D	20.90	21.00	21.10
E	15.70	15.80	15.90
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1			4.30
M	0.35		0.95
P	3.50	3.60	3.70
Q	5.60		6.00
S	6.05	6.15	6.25
aaa		0.04	0.10

Revision history

Table 9. **Document revision history**

Date	Revision	Changes
23-Jan-2025	1	First release.

Contents

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